Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				55	
I_H	I_T =100mA		MAX.	30	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	1000	V s
(dI/dt)c	G 9 G W F j=9150V 7		MIN.	3	A/ms
	40mA I_A=200mA I_R=20mA 25		TYP.	3	s
				30	

RACTERISTICS

Parameter		Value(MAX .)	Unit
=11A t_p=380 s	T_j=25	1.4	V
eshold voltage	T_j=150	0.78	V
amic resistance	T_j=150	55	P
=V_{DRM} V_R =V_{RRM}	T_j=25	5	A
	T_j=150	1	mA

ORDERING INFORMATION

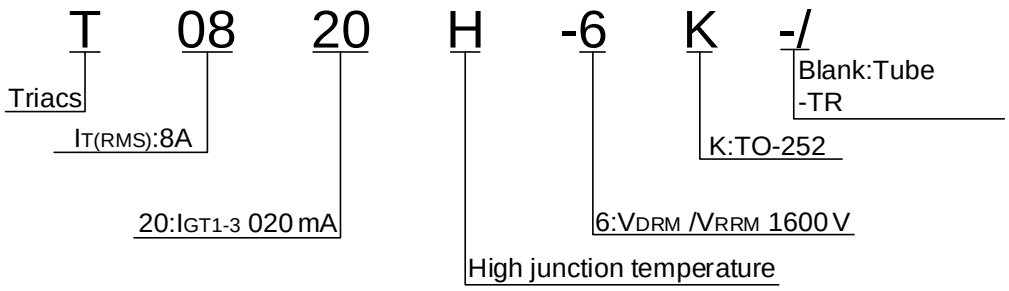


FIG.1: Maximum power dissipation versus RMS on-state current

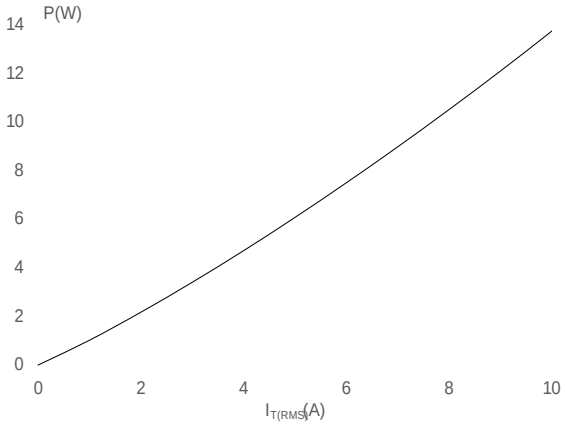


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

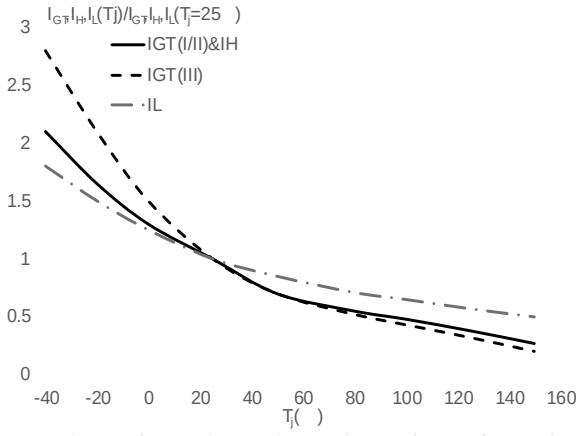


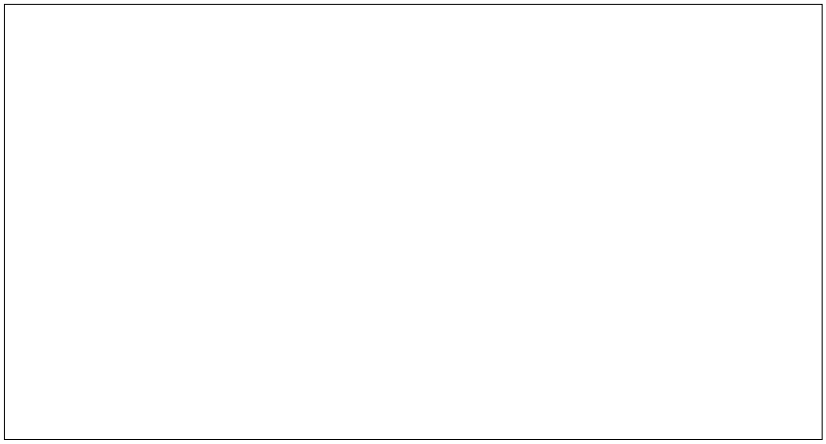
FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards

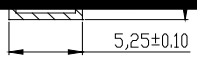
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	

PACKAGE MECHANICAL DATA

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
C	0.40		0.60	0.016		0.024
D						
E	6.40					
G						
G1						
L						




5,25±0.10

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